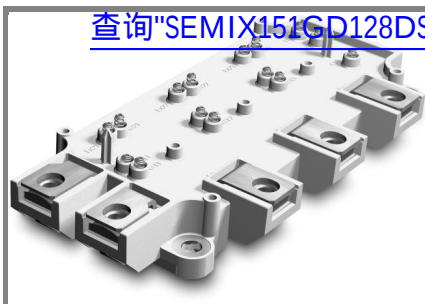


SEMiX 151GD128Ds

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SEMiX® 13s

SPT IGBT Modules

SEMiX 151GD128Ds

Preliminary Data

Features

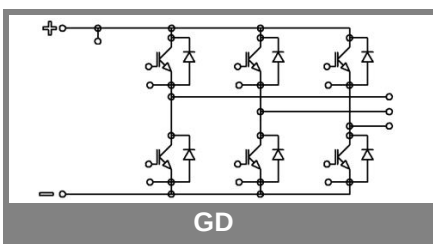
- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

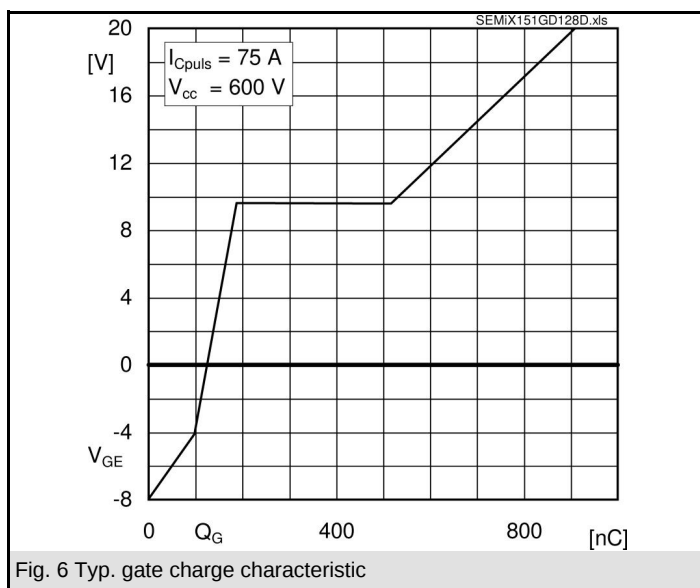
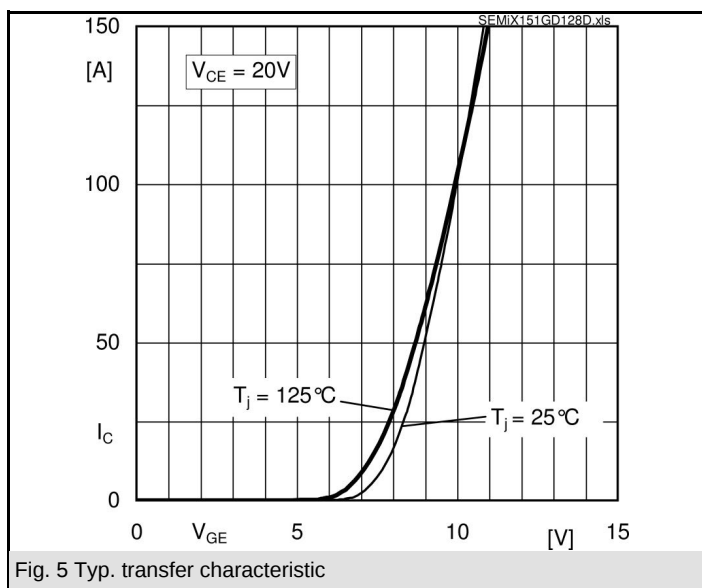
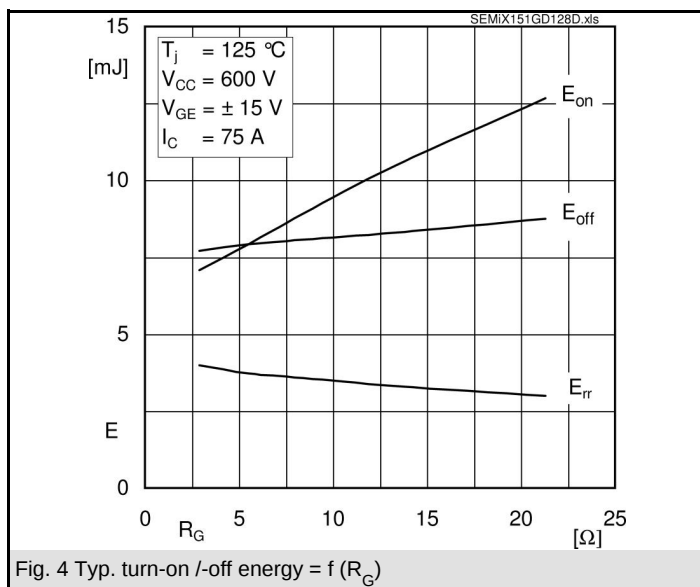
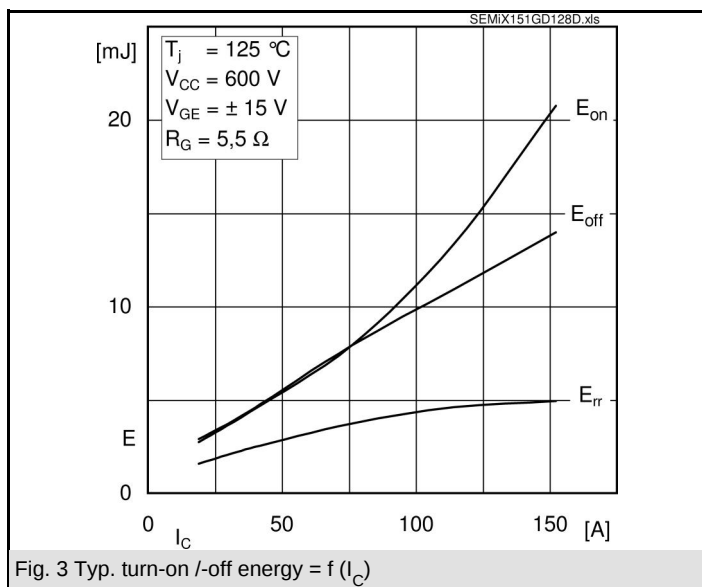
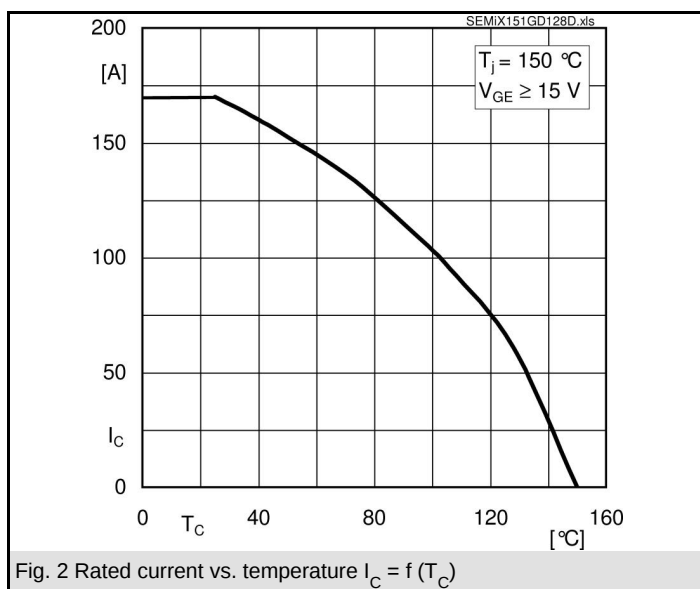
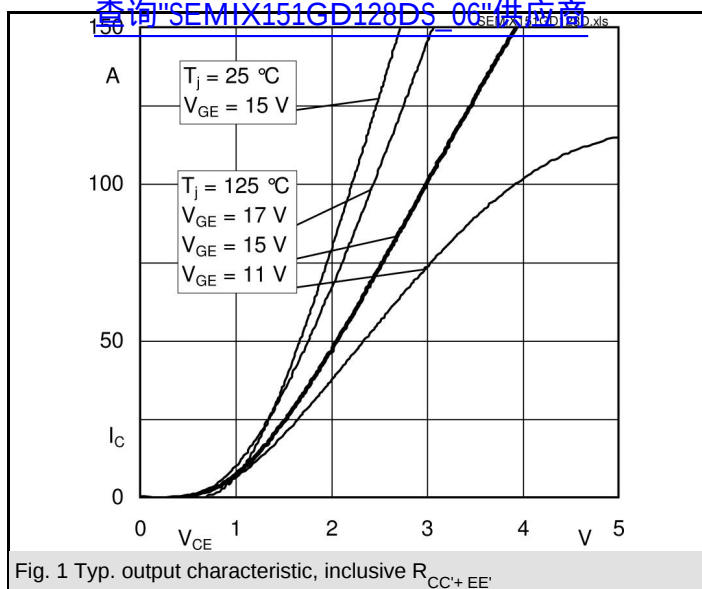
- AC inverter drives
- UPS
- Electronic welders f_{sw} up to 20 kHz

Absolute Maximum Ratings		$T_{case} = 25^{\circ}C$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^{\circ}C$	170 (130)	A
I_{CRM}	$t_p = 1 \text{ ms}$	150	A
V_{GES}		± 20	V
T_{vj} , (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^{\circ}C$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^{\circ}C$	100 (70)	A
I_{FRM}	$t_p = 1 \text{ ms}$	150	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 150^{\circ}C$	720	A

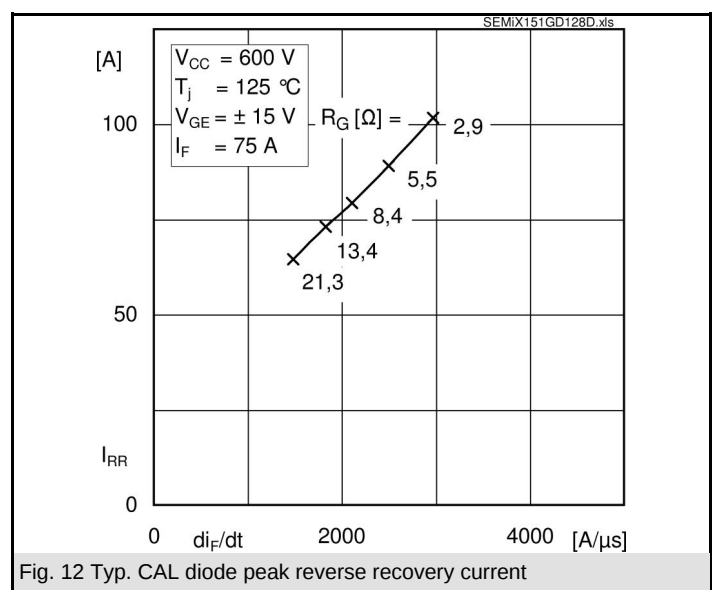
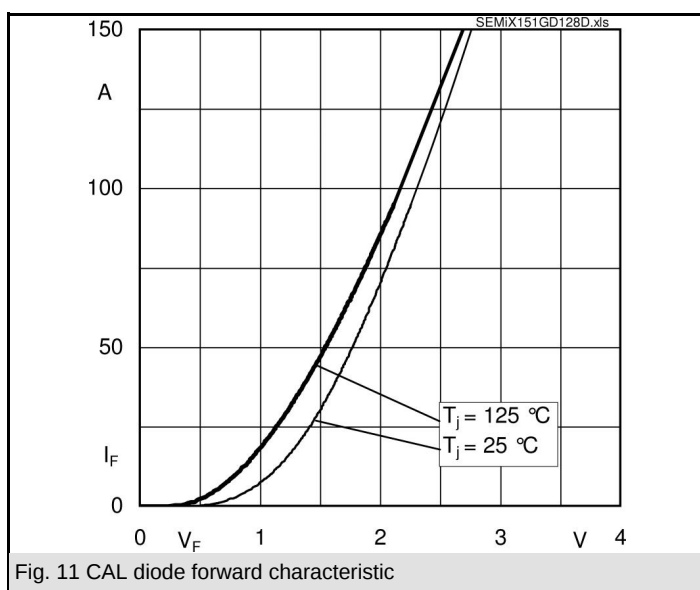
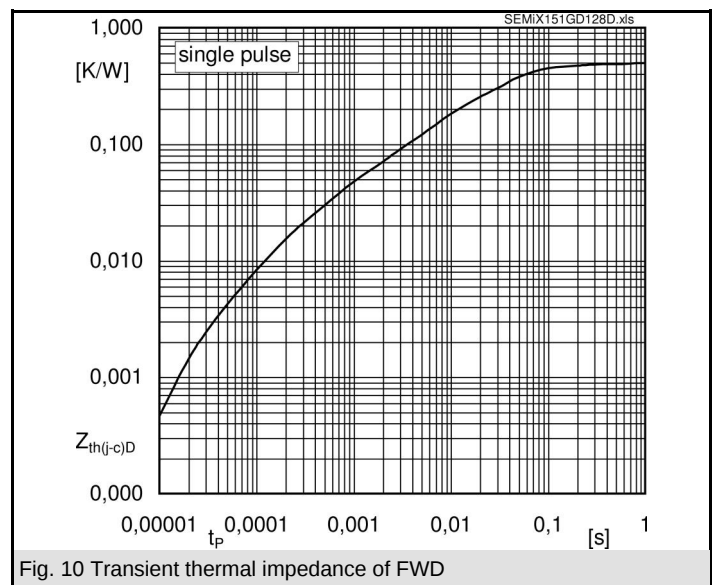
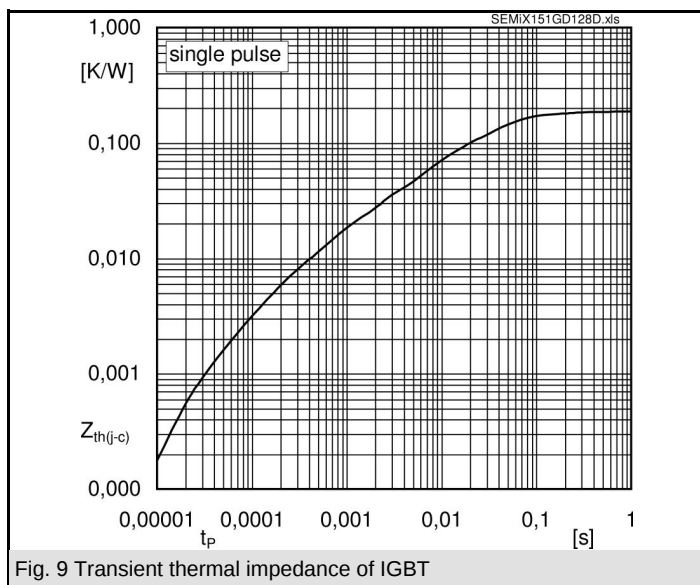
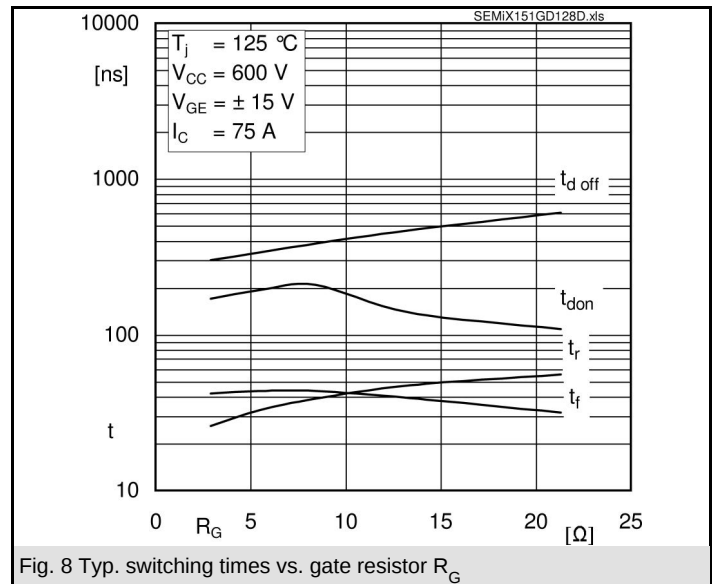
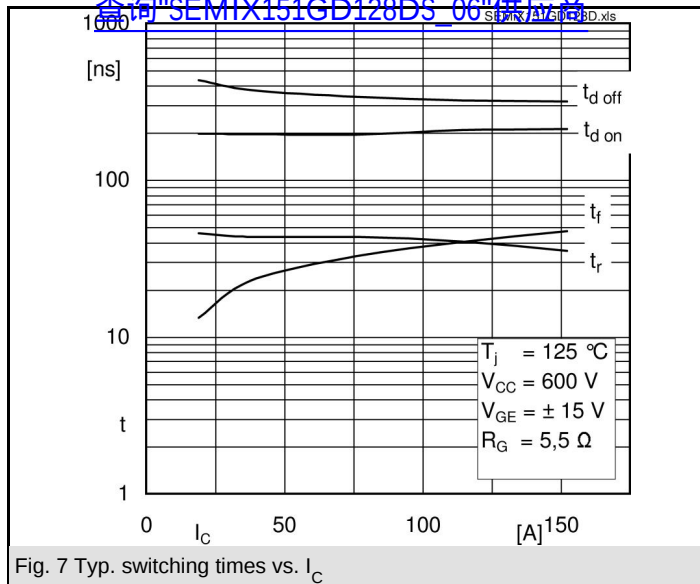
Characteristics		$T_{case} = 25^{\circ}C$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$	4,5	5	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25 (125)^{\circ}C$			0,3	mA
$V_{CE(TO)}$	$T_j = 25 (125)^{\circ}C$		1 (0,9)	1,15 (1,05)	V
r_{CE}	$V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^{\circ}C$		12 (15)	16 (20)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 75 \text{ A}$, $V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^{\circ}C$, chip level		1,9 (2,1)	2,35 (2,55)	V
C_{ies}	under following conditions		6,5		nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$		0,9		nF
C_{res}			0,8		nF
L_{CE}			20		nH
$R_{CC'+EE'}$	terminal-chip, $T_c = 25 (125)^{\circ}C$		0,7 (1)		m Ω
$t_{d(on)}/t_r$	$V_{CC} = 600 \text{ V}$, $I_{Cnom} = 75 \text{ A}$		200 / 33		ns
$t_{d(off)}/t_f$	$V_{GE} = \pm 15 \text{ V}$		330 / 44		ns
$E_{on} (E_{off})$	$R_{Gon} = R_{Goff} = 5,5 \Omega$, $T_j = 125^{\circ}C$		7,9 (7,9)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 75 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^{\circ}C$, chip level		2 (1,8)	2,5 (2,3)	V
$V_{(TO)}$	$T_j = 25 (125)^{\circ}C$		1,1	1,2	V
r_T	$T_j = 25 (125)^{\circ}C$		12	18	m Ω
I_{RRM}	$I_{Fnom} = 75 \text{ A}$; $T_j = 25 (125)^{\circ}C$		(90)		A
Q_{rr}	$di/dt = 2500 \text{ A}/\mu\text{s}$		(11)		μC
E_{rr}	$V_{GE} = -15 \text{ V}$		(3,5)		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,21	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,5	K/W
$R_{th(j-c)FD}$	per FWD				K/W
$R_{th(c-s)}$	per module		0,04		K/W
Temperature sensor					
R_{25}	$T_c = 25^{\circ}C$		5 $\pm$ 5%		k Ω
$B_{25/85}$	$R_2 = R_1 \exp[B(1/T_2 - 1/T_1)]$; $T[K]; B$		3420		K
Mechanical data					
M_s/M_t	to heatsink (M5) / for terminals (M6)	3/2,5		5 / 5	Nm
w			290		g

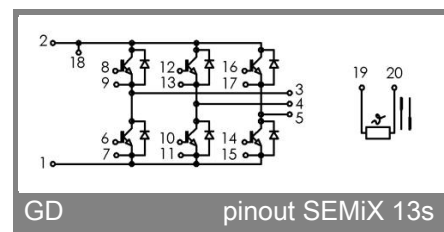
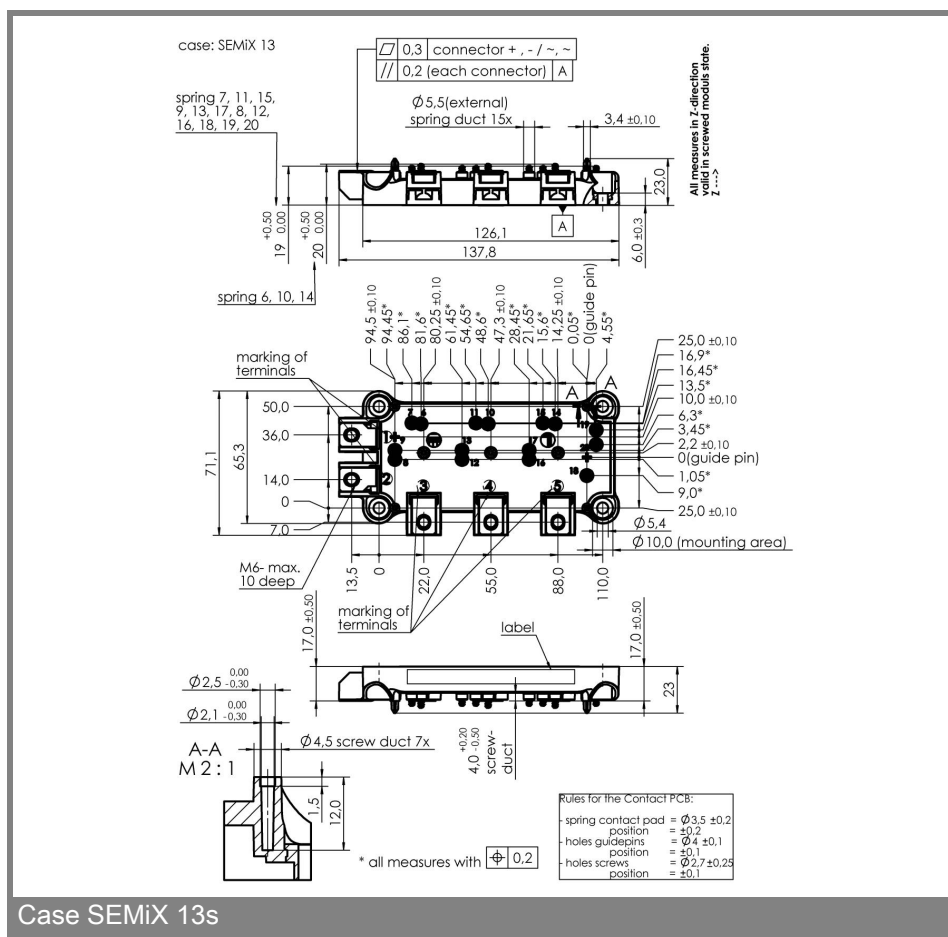
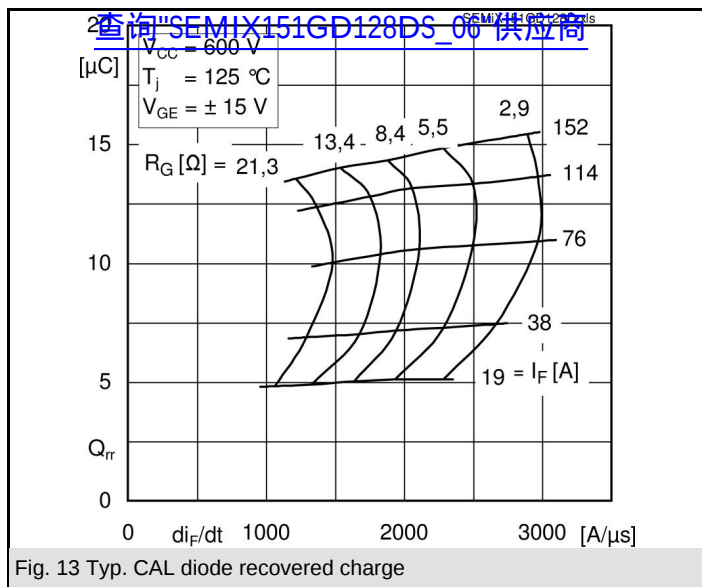


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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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